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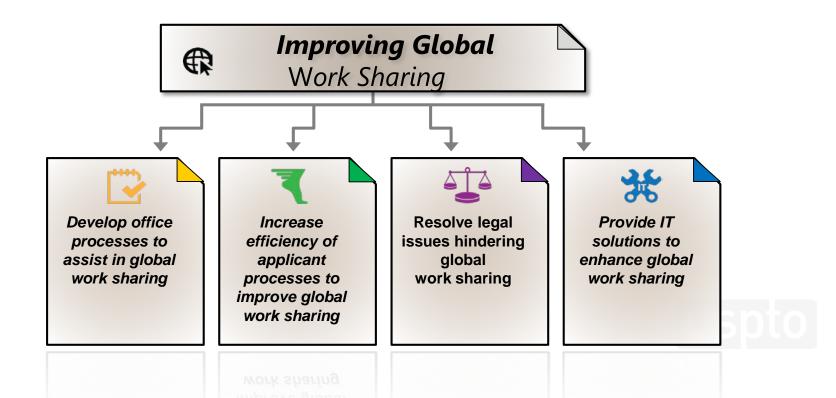


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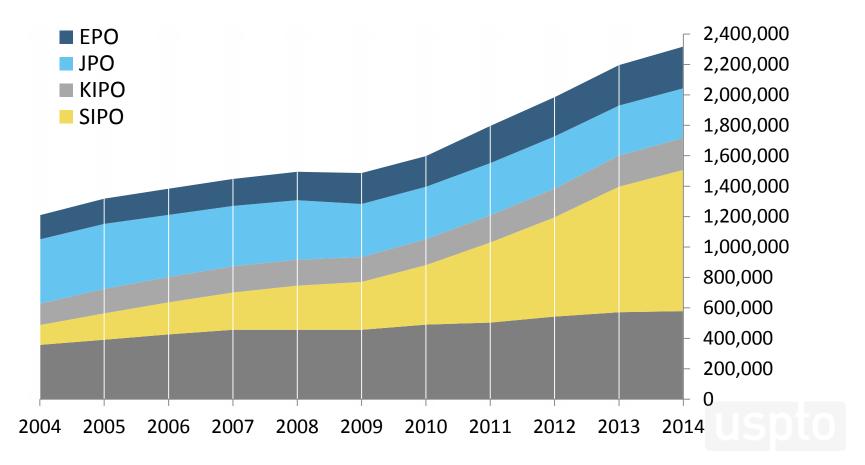
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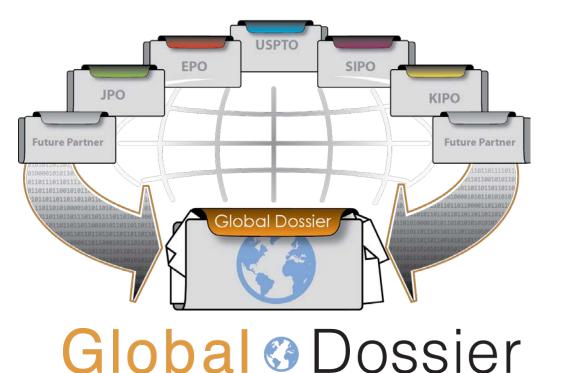
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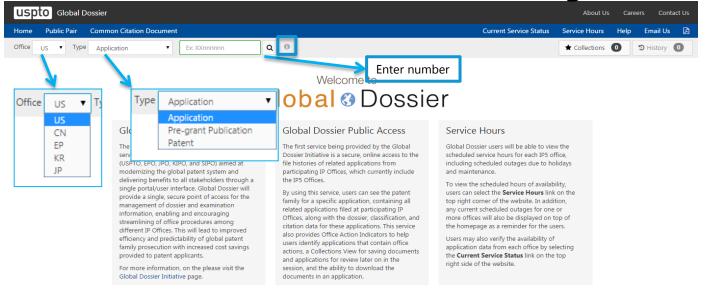
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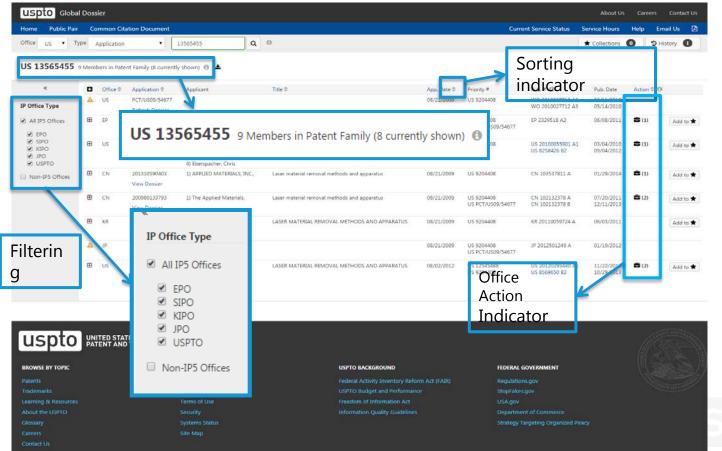
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	•	US	12545488	1) Zhang, Zhenhua 2) Rana, Virendra V 3) Shah, Vinay K, 4) Eberspacher, Ch	5.	LASER MATERIAL REMOVAL MET	HODS AND APPARATUS	08/21/2009	US 9204408	US 13565455			• *
			DATE	DOCUMENT DESCRIPTION @						EP 09811971			
			Aug 15, 2012	Issue Notification	()								-
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			Aug 1, 2012	Fee Worksheet (\$806)	(m)					Publication			
			All Documer	nts Classification and Citat	on					US 20070155322			
	8	CN	201310590403	1) APPLIED MATER	ALS, INC.	Laser material removal methods	and apparatus	08/21/2009	US 9204408	03 20070133322			
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			Apr 28, 2015	Claims (ORIGINAL)	-				Histo	ory of viewed	annlica	ations	
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		CN	200980133793	1) The Applied Mat	enals,	Laser material removal methods	and apparatus	08/21/2009	US 9204408	CN 102132378 A	07/20/2011	A (2)	Add to ★
									US PCT/US09/5467	7 CN 102132378 B	12/11/2013		

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102	Search information including classification, databases and other search related notes	07/06/2012		12545488 2013105904	102		PATTERSON & SHERIDAN, LLP APPM/TX	EXAMINER TRINK MICHAEL MANH		
101	List of References cited by applicant and considered by examiner	07/06/2012	CN	200980133	793		3040 POST OAK BOULEVARD, SUITE 1500 HOUSTON, TX 77056	ART UNIT PAPER NUMBER 2022		
101	List of References cited by applicant and considered by examiner	07/06/2012	KR	2011700657	76			DATE MAILEER 07/06/2012	_	
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5	Examiner's search strategy and results	07/06/2012	SRINT	-		2	· · · · · · · · · · · · · · · · · · ·		_	
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101	List of references cited by examiner	07/06/2012	897	-			PROSECUTION ON THE MERITS IS CLOSED. THIS NOT THIS APPLICATION IS SUBJECT TO WITHDRAWAL FR PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND M	ICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGI OM ISSUE AT THE INITIATIVE OF THE OFFICE OR U PEP 1308.	ITS. PON	
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4	Bibliographic Data Sheet	07/06/2012	818	-			I. Review the SMALI. ENTITY status shown above.			
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0	Fee Worksheet (S806)	04/27/2012					A. If the status is the same, pay the TOTAL FEE(S) DUE shown above.	A. Pay TOTAL FEE(S) DUE shown above, or		
2		04/27/2012	N417				B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or	B. If applicant claimed SMALL ENTITY status before, or is claiming SMALL ENTITY status, check box 5a on Part B - F Transmittal and pay the PUBLICATION FEE (if required) and	ee(s)	
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4	Applicant Arguments/Remarks Made in an Amendment	04/27/2012	REM	-			request to reapply a previously paid issue for must be clearly made the paper as an equivalent of Part B.	and delays in processing may occur due to the difficulty in recogn	iring	
4	Chime	04/27/2012	CINE .	1.00			III. All communications regarding this application must give the ap	plication number. Please direct all communications prior to issuan	ce to	

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B23K 26/08	
B23K 26/0846 {for moving elongated workpieces longitudinally, e.g. wire or strip material	il}
B23K 26/0853 {Devices involving movement of the workpiece in at least in two axial directio	ons, e.g. in a plane}
	,
B23K 26/0861 {in at least in three axial directions}	
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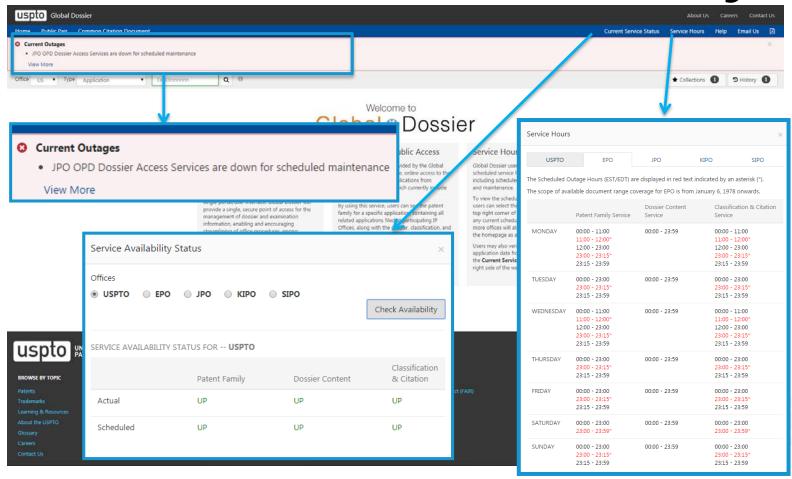


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Global Dossier Availability



Upcoming Features

- Enhanced Office Action indicator
- Document filtering
- Enhanced Office availability alerts
- Linkage with WIPO CASE
- PPH pilot



IP5 Priorities for Global Dossier

- USPTO "Proof-of-Concept for Inter-Office Exchange"
 - Sharing documents between offices including for example, prior art exchanges, bib data updates, and supporting documents. Viewed as a first step towards cross-filing
- EPO "Alerting"
 - Automated mechanism whereby each office alerts all the other offices, applicants, and representatives of changes in status to an application
- JPO "XML"
 - Enabling each office, and possibly applicants and representatives, to download all application-related data from applications pending in other offices in XML format
- KIPO "Applicant Name Standardization"
 - An automated mechanism that will assign a single, unique name to entities with applications pending in multiple office, including in instances where those entities may have used multiple names, or variations of a single name. to identify themselves
- SIPO -- "Legal Status"
 - A mechanism to allow users to view the legal status of an application in another office



Stakeholder Input on Global Dossier

- IdeaScale <u>http://uspto-globaldossier.ideascale.com/</u>
 - IdeaScale is one of the ways that OIPC will be gathering stakeholder input and feedback on Global Dossier.
 - Vote and comment on the various ideas
 - Provide additional suggestions for services and features that would improve the ability to monitor and manage related cases around the world
- Focus Sessions
 - Conducted to gather input and feedback on services
- Contact the Global Dossier Team
 - GlobalDossier@USPTO.gov



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Global Dossier Initiative

The Global Dossier Initiative is a set of business services being developed by the IPS Offices (USPTO, EPO, IPO, RPO, and SIPO) aimed at modernizing the global patent system and delivering benefits to all stakeholders through a single portulyser interface. Global Dossier will provide a single, secure point of access for the management of dossier and examination information, enabling and encouraging streamlining of office procedures among different IP Offices. This will lead to improved efficiency and predictability of global patent family prosecution with increased cost savings provided to patent applicants.

For more information, on the please visit the Global Dossier Initiative page.

Global Dossier Public Access

The first service being provided by the Global Dossier Initiative is a secure, online access to the file histories of related applications from participating IP Offices, which currently include the IP5 Offices.

By using this service, users can see the patent family for a specific application, containing all related applications field at participating IP Offices, along with the dosiser, classification, and clation data for these applications, this service also provides Office Action Indicators to help users identify applications that contain office and applications for review later on in the session, and the ability to download the documents in an application.

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Global Dossier Contacts

E-mail: GlobalDossier@USPTO.gov

Don Levin Director, International Patent Business Solutions 571-272-3785 <u>Don.Levin@USPTO.gov</u>

Nelson Yang

Patent Business Analyst, International Patent Business Solutions 571-272-0826 <u>Nelson.Yang@USPTO.gov</u>

Jessica Patterson

Program Manager, Office of International Patent Cooperation 571-272-8828 Jessica.Patterson@USPTO.gov



Access to Relevant Prior Art



Background

- USPTO is studying how to increase examination efficiency and patent quality through providing examiners with access to relevant prior art and supplemental information at the earliest point in examinations.
- Additionally, exploring whether or not automatically importing relevant prior art into the US application file at the earliest point in examination would improve prosecution efficiency and quality and reduce the burden of duty of disclosure for applicants.



Current Issues: Examiner Perspective

– Examiners

- <u>Awareness/availability</u>: how do examiners know that relevant prior art is available and how do they access it
- <u>Efficiently obtained</u>: how does the relevant prior art get to the examiner in a manner and time that will increase search and examination efficiency and quality
- <u>Value Recognition</u> what supplemental information is available to assist the examiner in determining the relevance of prior art



Current Issues: Applicant Perspective

– <u>Applicants</u>

- <u>Acquiring Information</u>: how do applicants efficiently obtaining the information necessary to meet their duty of disclosure and assist the examiner in making a proper patentability decision
- <u>Efficiently obtained</u>: how do applicants avoid cumbersome, costly, and time consuming efforts to monitor prosecution in related or counterpart applications or external sources so as to obtain relevant prior art
- <u>Compliant presentation</u>: how do applicants efficiently submit relevant prior art to the examiner in a time and manner such that it complies with relevant regulations



Anticipated Benefits

- Increase in patent quality
- Efficiency of examination is increased
- Examiner access to relevant prior art and supplemental information in a conveniently searchable manner
- Decreased applicant expense of submitting prior art documents and information disclosure statements
- Reduced burden for applicant compliance with duty to disclose information material to patentability

Timeline

- <u>Stage 1:</u> Three track parallel information gathering
 - <u>Track 1</u> IT & Data Source Gathering
 - <u>Track 2</u> Application Studies Data Gathering
 - <u>Track 3</u> Data gathering from internal and external stakeholders
- <u>Stage 2:</u> Information Review
- <u>Stage 2.5</u>: Business Solution Development
- <u>Stage 3:</u> IT Development and Implementation



Thank you!



